1. **(Currently amended)** A method of fabricating a field-effect transistor ~~device~~ on an integrated circuit, comprising the steps of:

providing a single-crystal silicon substrate;

forming a metal silicate dielectric layer on the substrate; and

forming a conductive transistor gate overlying the metal silicate dielectric layer.

2. - 30. (canceled).

31. - 35. (canceled).

36. - 40. (canceled).

41. - 45. (canceled).

46. **(currently amended, with rejoinder requested)** A method of fabricating a field-effect transistor ~~device~~ on an integrated circuit, comprising the steps of:

providing a single-crystal silicon substrate;

forming a zirconium silicate dielectric layer on the substrate; and

forming a conductive transistor gate overlying the zirconium silicate dielectric layer.

47. - 70. (canceled).

71. **(withdrawn, with rejoinder requested)** The method of claim 46, wherein the forming a zirconium silicate dielectric layer step comprises:

exposing a clean Si surface on the substrate; and

depositing a partially reduced zirconium silicate layer on the Si surface.

72. **(withdrawn, with rejoinder requested)** The method of claim 71, further comprising annealing the partially reduced zirconium silicate layer substrate in oxygen, thereby forming the zirconium silicate dielectric layer.

73. **(withdrawn, with rejoinder requested)** The method of claim 72, wherein the depositing a partially reduced zirconium silicate layer on the Si surface comprises simultaneous physical vapor deposition of zirconium oxide and silicon.

74. - 80. (canceled).